

P-Channel Enhancement-Mode MOSFET

DESIGNED FOR:

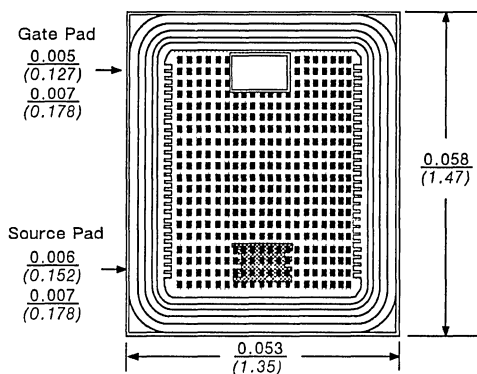
- Switching
- Amplification

FEATURES

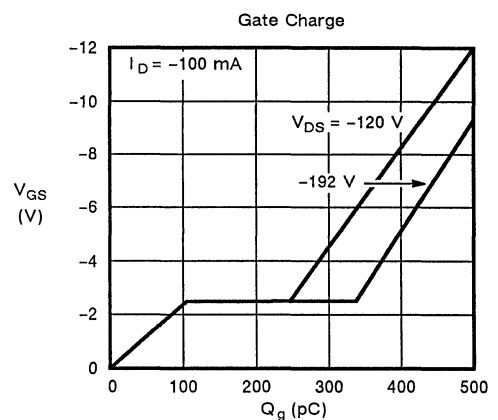
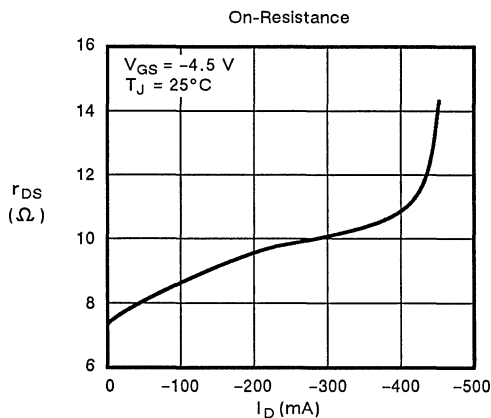
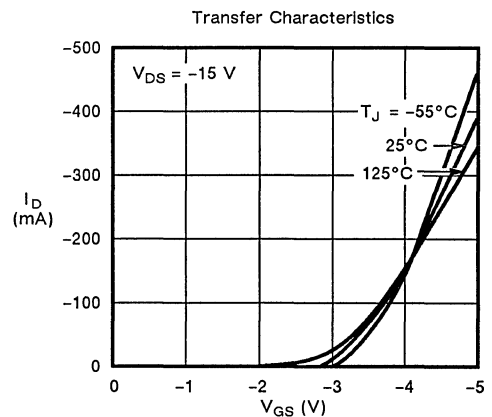
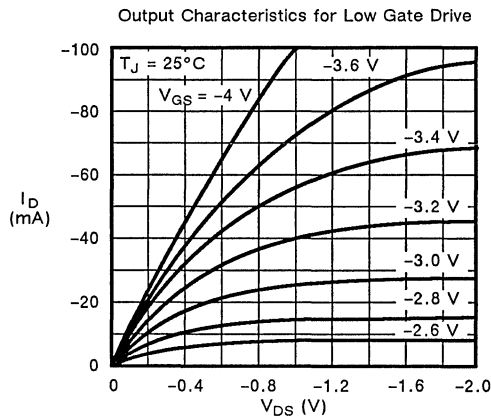
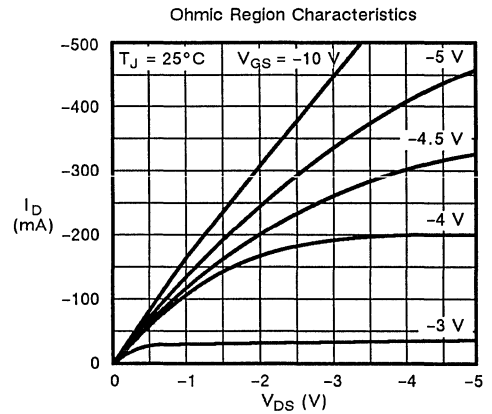
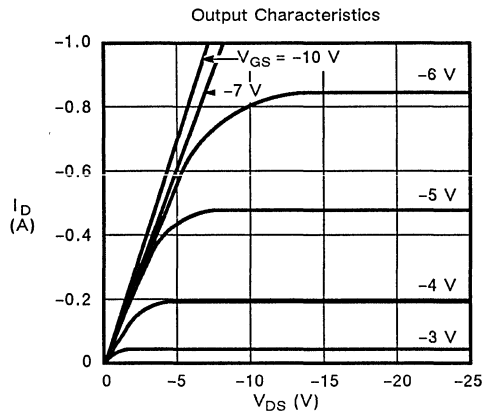
- High Breakdown > 240 V
- Low $r_{DS(on)} < 10 \Omega$

TYPE	PACKAGE	DEVICE
Single	TO-205AD	• VP2410B
	TO-92	• VP2410L BS208
	Chip	• Available as above specifications

GEOMETRY DIAGRAM

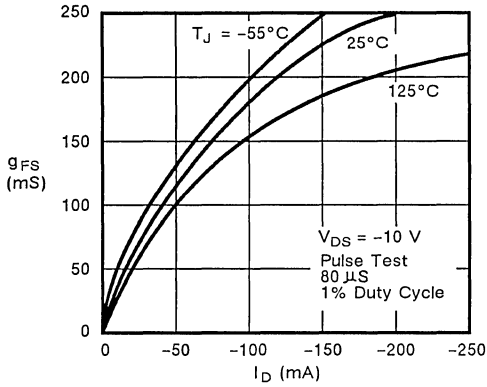


TYPICAL CHARACTERISTICS

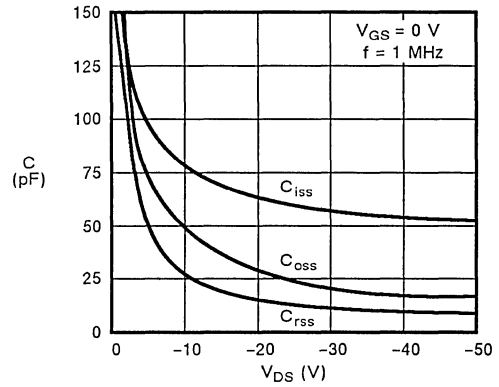


TYPICAL CHARACTERISTICS

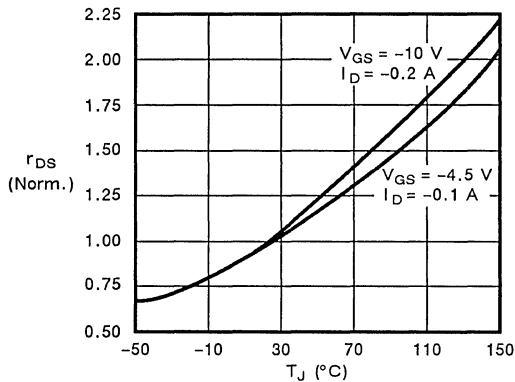
Transconductance



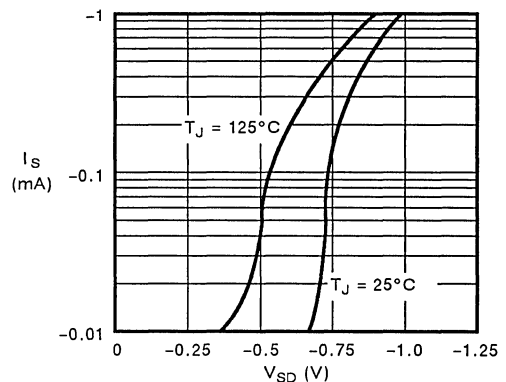
Capacitance



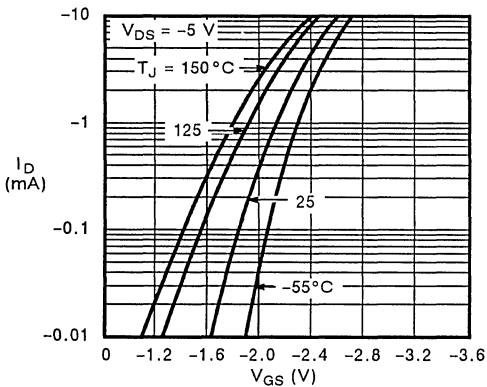
On-Resistance vs. Junction Temperature



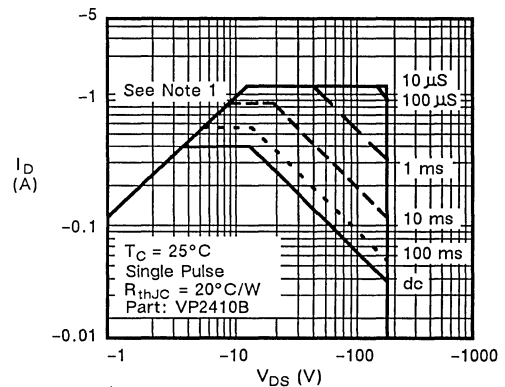
Source-Drain Diode Forward Voltage



Threshold Region

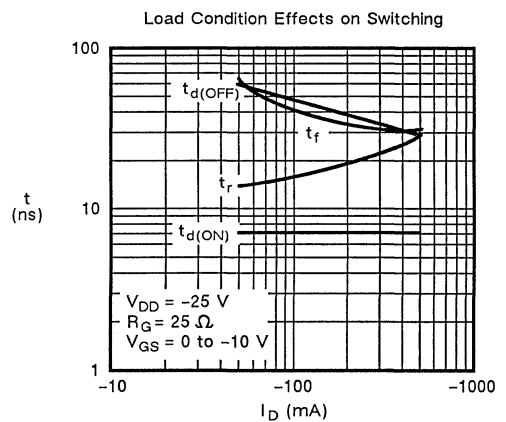
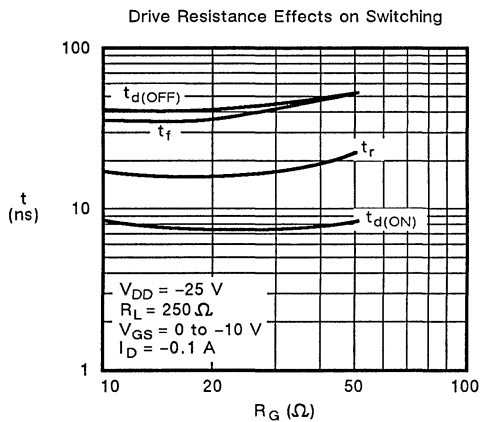
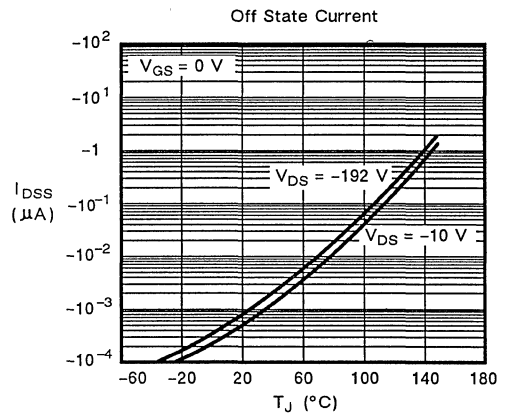
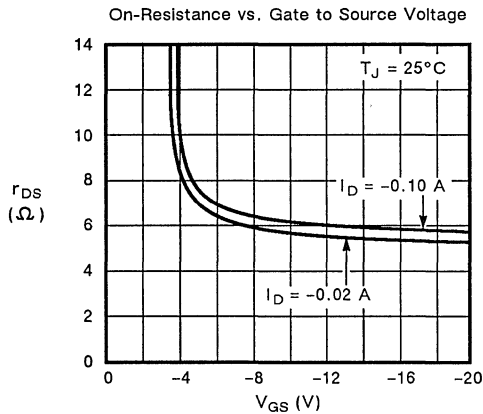
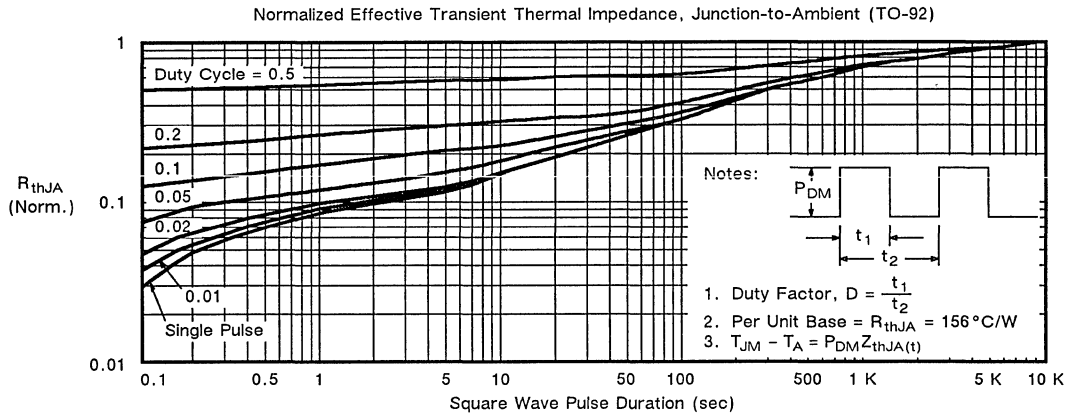


Safe Operating Area



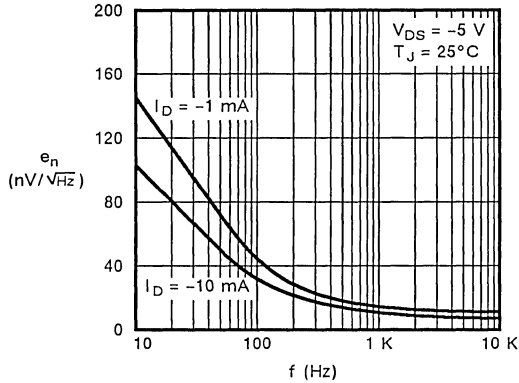
¹Operation in this area may be limited by $r_{DS(ON)}$

TYPICAL CHARACTERISTICS

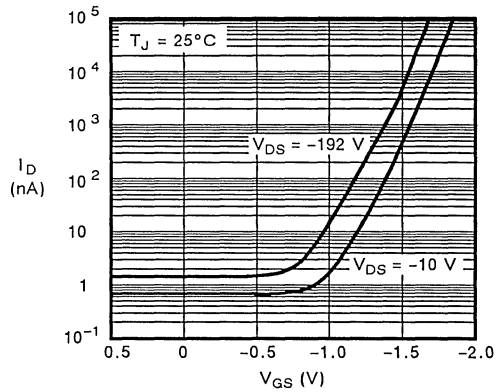


TYPICAL CHARACTERISTICS

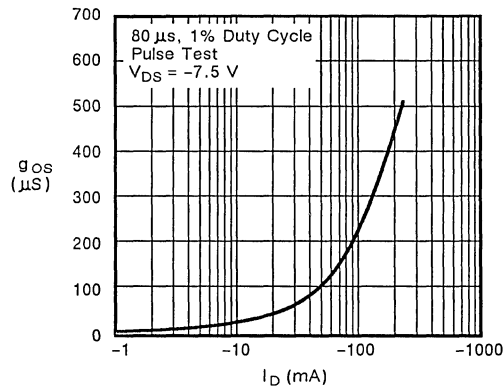
Equivalent Input Noise Voltage vs. Frequency



Body Drain Leakage Current



Output Conductance vs. Drain Current



Transient Thermal Response (TO-205AD)

